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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

270 papers	3,856 citations	33 h-index	48 g-index
304 ext. papers	4,382 ext. citations	1.9 avg, IF	5.71 L-index

#	Paper	IF	Citations
270	Nearly Ideal Current/Voltage Characteristics of Schottky Barrier Diodes Formed on Hydride-Vapor-Phase-Epitaxy-Grown GaN Free-Standing Substrates. <i>Applied Physics Express</i> , 2010 , 3, 101003	2.4	106
269	Lifetime-killing defects in 4H-SiC epilayers and lifetime control by low-energy electron irradiation. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 1327-1336	1.3	96
268	Characterization of stacking faults in 4H-SiC epilayers by room-temperature microphotoluminescence mapping. <i>Applied Physics Letters</i> , 2008 , 92, 221906	3.4	92
267	Ultrahigh-Voltage SiC p-i-n Diodes With Improved Forward Characteristics. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 374-381	2.9	88
266	Zirconium Diboride (0001) as an Electrically Conductive Lattice-Matched Substrate for Gallium Nitride. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L1280-L1282	1.4	85
265	21-kV SiC BJTs With Space-Modulated Junction Termination Extension. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1598-1600	4.4	82
264	Space-Modulated Junction Termination Extension for Ultrahigh-Voltage p-i-n Diodes in 4H-SiC. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 414-418	2.9	76
263	Temperature and doping dependencies of electrical properties in Al-doped 4H-SiC epitaxial layers. <i>Journal of Applied Physics</i> , 2009 , 106, 013716	2.5	73
262	Impacts of recombination at the surface and in the substrate on carrier lifetimes of n-type 4H-SiC epilayers. <i>Journal of Applied Physics</i> , 2010 , 108, 083721	2.5	60
261	Triple Shockley type stacking faults in 4H-SiC epilayers. <i>Applied Physics Letters</i> , 2009 , 94, 091910	3.4	60
260	Simulation and Experimental Study on the Junction Termination Structure for High-Voltage 4H-SiC PiN Diodes. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1841-1846	2.9	60
259	Highly effective activation of Mg-implanted p-type GaN by ultra-high-pressure annealing. <i>Applied Physics Letters</i> , 2019 , 115, 142104	3.4	58
258	4H-SiC MISFETs with nitrogen-containing insulators. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 2374-2390	1.6	58
257	Analytical model for reduction of deep levels in SiC by thermal oxidation. <i>Journal of Applied Physics</i> , 2012 , 111, 053710	2.5	57
256	21.7 kV 4H-SiC PiN Diode with a Space-Modulated Junction Termination Extension. <i>Applied Physics Express</i> , 2012 , 5, 064001	2.4	56
255	Characterization of major in-grown stacking faults in 4H-SiC epilayers. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4745-4748	2.8	55
254	Impact Ionization Coefficients in 4H-SiC Toward Ultrahigh-Voltage Power Devices. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 3326-3333	2.9	53

253	Interface Properties of 4H-SiC ($11\bar{2}0$) and ($1\bar{1}00$) MOS Structures Annealed in NO. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 309-315	2.9	52
252	Effects of Nitridation on 4H-SiC MOSFETs Fabricated on Various Crystal Faces. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1260-1262	2.9	48
251	Hall-effect measurements of metalorganic vapor-phase epitaxy-grown p-type homoepitaxial GaN layers with various Mg concentrations. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 031001	1.4	46
250	High-Quality AlN by Initial Layer-by-Layer Growth on Surface-Controlled 4H-SiC(0001) Substrate. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L445-L447	1.4	46
249	Design and Fabrication of GaN p-n Junction Diodes With Negative Beveled-Mesa Termination. <i>IEEE Electron Device Letters</i> , 2019 , 40, 941-944	4.4	45
248	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. <i>Applied Physics Letters</i> , 2013 , 102, 112106	3.4	44
247	4H-SiC BJT With Record Current Gains of 257 on (0001) and 335 on ($1\bar{1}00$). <i>IEEE Electron Device Letters</i> , 2011 , 32, 841-843	4.4	43
246	Carrier Recombination in n-Type 4H-SiC Epilayers with Long Carrier Lifetimes. <i>Applied Physics Express</i> , 2012 , 5, 101301	2.4	43
245	High temperature annealing of n-type 4H-SiC: Impact on intrinsic defects and carrier lifetime. <i>Journal of Applied Physics</i> , 2012 , 111, 033515	2.5	43
244	Sources of carrier compensation in metalorganic vapor phase epitaxy-grown homoepitaxial n-type GaN layers with various doping concentrations. <i>Applied Physics Express</i> , 2018 , 11, 041001	2.4	41
243	P-Channel MOSFETs on 4H-SiC {0001} and Nonbasal Faces Fabricated by Oxide Deposition and N_2O Annealing. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 1953-1958	2.9	36
242	Experimental and theoretical investigations on short-channel effects in 4H-SiC MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 1954-1962	2.9	36
241	4H-SiC Lateral Double RESURF MOSFETs With Low on Resistance. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 1216-1223	2.9	35
240	Growth of AlN $11\bar{2}0$ on 6H-SiC $11\bar{2}0$ by Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, L1348-L1350	1.4	35
239	High-quality nonpolar 4H-AlN grown on 4H-SiC (1120) substrate by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2006 , 89, 112117	3.4	34
238	Quantitative comparison between Z1 center and carbon vacancy in 4H-SiC. <i>Journal of Applied Physics</i> , 2014 , 115, 143705	2.5	33
237	Breakdown Characteristics of 15-kV-Class 4H-SiC PiN Diodes With Various Junction Termination Structures. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 2748-2752	2.9	33
236	Deep levels induced by reactive ion etching in n- and p-type 4H-SiC. <i>Journal of Applied Physics</i> , 2010 , 108, 023706	2.5	32

- 235 1580-V Ω - Ω cm² Double-RESURF MOSFETs on 4H-SiC $\bar{1}11$. *IEEE Electron Device Letters*, **2009**, 30, 831-833 4.4 32
- 234 Time-resolved nonlinear luminescence of biexcitons in ZnSe-ZnMg_{1-x}SySe_{1-y} single quantum wells. *Physical Review B*, **1995**, 52, R2289-R2292 3.3 32
- 233 Molecular-beam epitaxial growth of insulating AlN on surface-controlled 6H-SiC substrate by HCl gas etching. *Applied Physics Letters*, **2002**, 80, 76-78 3.4 31
- 232 Improvement of Current Gain in 4H-SiC BJTs by Surface Passivation With Deposited Oxides Nitrided in N_2O or NO. *IEEE Electron Device Letters*, **2011**, 32, 285-287 4.4 30
- 231 Progress on and challenges of p-type formation for GaN power devices. *Journal of Applied Physics*, **2020**, 128, 090901 2.5 30
- 230 Temperature dependence of barrier height in Ni/n-GaN Schottky barrier diode. *Applied Physics Express*, **2017**, 10, 051002 2.4 29
- 229 Accurate measurements of second-order nonlinear optical coefficients of 6H and 4H silicon carbide. *Journal of the Optical Society of America B: Optical Physics*, **2009**, 26, 1892 1.7 29
- 228 Deep-level transient spectroscopy studies of electron and hole traps in n-type GaN homoepitaxial layers grown by quartz-free hydride-vapor-phase epitaxy. *Applied Physics Letters*, **2019**, 115, 012103 3.4 28
- 227 Reduction of deep levels generated by ion implantation into n- and p-type 4H-SiC. *Journal of Applied Physics*, **2010**, 108, 033706 2.5 28
- 226 Improved Dielectric and Interface Properties of 4H-SiC MOS Structures Processed by Oxide Deposition and N₂O Annealing. *Materials Science Forum*, **2006**, 527-529, 987-990 0.4 27
- 225 1330 V, 67 m/spl Ω cm²/ 4H-SiC(0001) RESURF MOSFET. *IEEE Electron Device Letters*, **2005**, 26, 649-651 4.4 27
- 224 Control of carrier lifetime of thick n-type 4H-SiC epilayers by high-temperature Ar annealing. *Applied Physics Express*, **2016**, 9, 061303 2.4 27
- 223 Promise and Challenges of High-Voltage SiC Bipolar Power Devices. *Energies*, **2016**, 9, 908 3.1 26
- 222 Over-700-nm Critical Thickness of AlN Grown on 6H-SiC(0001) by Molecular Beam Epitaxy. *Applied Physics Express*, **2012**, 5, 105502 2.4 25
- 221 Ultrahigh-Voltage SiC MPS Diodes With Hybrid Unipolar/Bipolar Operation. *IEEE Transactions on Electron Devices*, **2017**, 64, 874-881 2.9 24
- 220 Interface state density of SiO₂/p-type 4H-SiC (0001), (1120), (1100) metal-oxide-semiconductor structures characterized by low-temperature subthreshold slopes. *Applied Physics Letters*, **2016**, 108, 152108 3.4 24
- 219 Enhancement of carrier lifetime in lightly Al-doped p-type 4H-SiC epitaxial layers by combination of thermal oxidation and hydrogen annealing. *Applied Physics Express*, **2014**, 7, 085501 2.4 23
- 218 Reduction of Threading Dislocation Density in 2H-AlN Grown on 6H-SiC(0001) by Minimizing Unintentional Active-Nitrogen Exposure before Growth. *Applied Physics Express*, **2011**, 4, 025502 2.4 23

217	Impact ionization coefficients and critical electric field in GaN. <i>Journal of Applied Physics</i> , 2021 , 129, 185703	2.3	23
216	Correlation between shapes of Shockley stacking faults and structures of basal plane dislocations in 4H-SiC epilayers. <i>Philosophical Magazine</i> , 2017 , 97, 2736-2752	1.6	22
215	Doping-Induced Lattice Mismatch and Misorientation in 4H-SiC Crystals. <i>Materials Science Forum</i> , 2012 , 717-720, 481-484	0.4	22
214	Hall scattering factors in p-type 4H-SiC with various doping concentrations. <i>Applied Physics Express</i> , 2016 , 9, 041301	2.4	22
213	Identification of dislocations in 4H-SiC epitaxial layers and substrates using photoluminescence imaging. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 020304	1.4	21
212	4H-SiC pn Photodiodes with Temperature-Independent Photoresponse up to 300 $^{\circ}$ C. <i>Applied Physics Express</i> , 2012 , 5, 094101	2.4	21
211	Enhancement of Carrier Lifetimes in n-Type 4H-SiC Epitaxial Layers by Improved Surface Passivation. <i>Applied Physics Express</i> , 2010 , 3, 121201	2.4	21
210	Improvement of Channel Mobility in Inversion-Type n-Channel GaN MetalOxideSemiconductor Field-Effect Transistor by High-Temperature Annealing. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 7784-7787	1.4	21
209	Defect evolution in Mg ions implanted GaN upon high temperature and ultrahigh N ₂ partial pressure annealing: Transmission electron microscopy analysis. <i>Journal of Applied Physics</i> , 2020 , 127, 105106	2.5	20
208	Electric-field-induced simultaneous diffusion of Mg and H in Mg-doped GaN prepared using ultra-high-pressure annealing. <i>Applied Physics Express</i> , 2019 , 12, 111005	2.4	19
207	Ion implantation technology in SiC for power device applications 2014 ,		19
206	Temperature Dependence of Impact Ionization Coefficients in 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 461-466	0.4	19
205	ZrB ₂ Substrate for Nitride Semiconductors. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 2260-2264	1.4	19
204	Overview of carrier compensation in GaN layers grown by MOVPE: toward the application of vertical power devices. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SA0804	1.4	19
203	Electrical properties of n- and p-type 4H-SiC formed by ion implantation into high-purity semi-insulating substrates. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 070306	1.4	18
202	Nonradiative recombination at threading dislocations in 4H-SiC epilayers studied by micro-photoluminescence mapping. <i>Journal of Applied Physics</i> , 2011 , 110, 033525	2.5	18
201	Lattice relaxation process of AlN growth on atomically flat 6H-SiC substrate in molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2002 , 237-239, 1012-1016	1.6	18
200	Redistribution of Mg and H atoms in Mg-implanted GaN through ultra-high-pressure annealing. <i>Applied Physics Express</i> , 2020 , 13, 086501	2.4	18

199	. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2054-2060	2.9	17
198	Accurate method for estimating hole trap concentration in n-type GaN via minority carrier transient spectroscopy. <i>Applied Physics Express</i> , 2018 , 11, 071002	2.4	16
197	Effect of ultrathin AlN spacer on electronic properties of GaN/SiC heterojunction bipolar transistors. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 034101	1.4	16
196	Accurate measurement of quadratic nonlinear-optical coefficients of gallium nitride. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2010 , 27, 2026	1.7	16
195	Gas-Source Molecular Beam Epitaxial Growth of (Zn, Mg)(S, Se) Using Bis-methylcyclopentadienyl-magnesium and Hydrogen Sulfide. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, L290-L293	1.4	16
194	Reduction of interface state density in SiC (0001) MOS structures by post-oxidation Ar annealing at high temperature. <i>AIP Advances</i> , 2017 , 7, 045008	1.5	15
193	Improvement of Carrier Lifetimes in Highly Al-Doped p-Type 4H-SiC Epitaxial Layers by Hydrogen Passivation. <i>Applied Physics Express</i> , 2013 , 6, 121301	2.4	15
192	Optical Properties of ZnSe/ZnMgSSe Single Quantum Wells Grown by Metalorganic Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, L986-L989	1.4	15
191	Reduction of plasma-induced damage in n-type GaN by multistep-bias etching in inductively coupled plasma reactive ion etching. <i>Applied Physics Express</i> , 2020 , 13, 016505	2.4	15
190	Impact Ionization Coefficients in GaN Measured by Above- and Sub-Eg Illuminations for p ⁺ n ⁺ Junction 2019 ,		15
189	Measurement of avalanche multiplication utilizing Franz-Keldysh effect in GaN p-n junction diodes with double-side-depleted shallow bevel termination. <i>Applied Physics Letters</i> , 2019 , 115, 142101	3.4	14
188	Identification of origin of E C 0.6 eV electron trap level by correlation with iron concentration in n-type GaN grown on GaN freestanding substrate by metalorganic vapor phase epitaxy. <i>Applied Physics Express</i> , 2020 , 13, 071007	2.4	14
187	Deep levels generated by thermal oxidation in p-type 4H-SiC. <i>Journal of Applied Physics</i> , 2013 , 113, 033705	2.5	14
186	Single-crystalline 4H-SiC micro cantilevers with a high quality factor. <i>Sensors and Actuators A: Physical</i> , 2013 , 197, 122-125	3.9	14
185	Ultrahigh-Voltage (> 20 kV) SiC PiN Diodes with a Space-Modulated JTE and Lifetime Enhancement Process via Thermal Oxidation. <i>Materials Science Forum</i> , 2014 , 778-780, 832-835	0.4	14
184	Quantum-confinement effect on holes in silicon nanowires: Relationship between wave function and band structure. <i>Journal of Applied Physics</i> , 2011 , 109, 064318	2.5	14
183	Enhancement of initial layer-by-layer growth and reduction of threading dislocation density by optimized Ga pre-irradiation in molecular-beam epitaxy of 2H-AlN on 6H-SiC(0001). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2094-2096		14
182	Franz-Keldysh effect in GaN p-n junction diode under high reverse bias voltage. <i>Applied Physics Letters</i> , 2018 , 112, 252104	3.4	13

181	Shockley-Read-Hall lifetime in homoepitaxial p-GaN extracted from recombination current in GaN p ⁺ n junction diodes. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCB14	1.4	12
180	Formation mechanism of threading-dislocation array in AlN layers grown on 6H-SiC (0001) substrates with 3-bilayer-high surface steps. <i>Applied Physics Letters</i> , 2014 , 105, 071603	3.4	12
179	Sources of Epitaxial Growth-Induced Stacking Faults in 4H-SiC. <i>Journal of Electronic Materials</i> , 2010 , 39, 1166-1169	1.9	12
178	Thermo-Optic Coefficients of 4H-SiC, GaN, and AlN for Ultraviolet to Infrared Regions up to 500 °C. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 112101	1.4	12
177	Effects of 6H-SiC surface reconstruction on lattice relaxation of AlN buffer layers in molecular-beam epitaxial growth of GaN. <i>Applied Physics Letters</i> , 2002 , 81, 5141-5143	3.4	11
176	Growth evolution of cubic-GaN on sapphire (0001) substrate by metalorganic molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1999 , 201-202, 437-440	1.6	11
175	Mg-implanted bevel edge termination structure for GaN power device applications. <i>Applied Physics Letters</i> , 2021 , 118, 093502	3.4	11
174	. <i>IEEE Electron Device Letters</i> , 2014 , 35, 339-341	4.4	10
173	Defect Control in Growth and Processing of 4H-SiC for Power Device Applications. <i>Materials Science Forum</i> , 2010 , 645-648, 645-650	0.4	10
172	Comprehensive analysis of multiple-reflection effects on rotational Maker-fringe experiments. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2008 , 25, 1616	1.7	10
171	Why do electron traps at E _C - 0.6 eV have inverse correlation with carbon concentrations in n-type GaN layers?. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 105505	1.4	10
170	Surface passivation on 4H-SiC epitaxial layers by SiO ₂ with POCl ₃ annealing. <i>Applied Physics Express</i> , 2016 , 9, 051301	2.4	10
169	Interface properties of NO-annealed 4H-SiC (0001), (1120), and (1100) MOS structures with heavily doped p-bodies. <i>Journal of Applied Physics</i> , 2017 , 121, 145703	2.5	9
168	Phonon-Limited Electron Mobility in Rectangular Cross-Sectional Ge Nanowires. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1993-1998	2.9	9
167	Orientation and Shape Effects on Ballistic Transport Properties in Gate-All-Around Rectangular Germanium Nanowire nFETs. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 944-950	2.9	9
166	Breakdown characteristics of 1200 kV-class 4H-SiC PiN diodes with improved junction termination structures 2012 ,		9
165	Optical Properties of Highly Strained AlN Coherently Grown on 6H-SiC(0001). <i>Applied Physics Express</i> , 2013 , 6, 062604	2.4	9
164	Deep Levels Generated by Thermal Oxidation in n-Type 4H-SiC. <i>Applied Physics Express</i> , 2013 , 6, 051301	2.4	9

163	Mobility oscillation by one-dimensional quantum confinement in Si-nanowire metal-oxide-semiconductor field effect transistors. <i>Journal of Applied Physics</i> , 2009 , 106, 034312	2.5	9
162	4H-SiC bipolar junction transistors with record current gains of 257 on (0001) and 335 on (000 $\bar{1}$) 2011 ,		9
161	Enhanced Current Gain (>250) in 4H-SiC Bipolar Junction Transistors by a Deep-Level-Reduction Process. <i>Materials Science Forum</i> , 2012 , 717-720, 1117-1122	0.4	9
160	Nonpolar 4H-AlN grown on 4H-SiC (11 $\bar{2}00$) with reduced stacking fault density realized by persistent layer-by-layer growth. <i>Applied Physics Letters</i> , 2008 , 93, 082106	3.4	9
159	Improved Performance of 4H-SiC Double Reduced Surface Field MetalOxideSemiconductor Field-Effect Transistors by Increasing RESURF Doses. <i>Applied Physics Express</i> , 2008 , 1, 101403	2.4	9
158	Scanning Capacitance and Spreading Resistance Microscopy of SiC Multiple-pn-Junction Structure. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, L40-L42	1.4	9
157	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. <i>Scientific Reports</i> , 2020 , 10, 17349	4.9	9
156	Temperature dependence of optical absorption coefficient of 4H- and 6H-SiC from room temperature to 300 °C. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 108003	1.4	8
155	Nondestructive Visualization of Individual Dislocations in 4H-SiC Epilayers by Micro Photoluminescence Mapping. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 090201	1.4	8
154	Enhanced Drain Current of 4H-SiC MOSFETs by Adopting a Three-Dimensional Gate Structure. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2632-2637	2.9	8
153	Enhanced Channel Mobility in 4H-SiC MISFETs by Utilizing Deposited SiN/SiO ₂ Stack Gate Structures. <i>Materials Science Forum</i> , 2008 , 600-603, 679-682	0.4	8
152	High Channel Mobilities of MOSFETs on Highly-Doped 4H-SiC (11-20) Face by Oxidation in N ₂ O Ambient. <i>Materials Science Forum</i> , 2004 , 457-460, 1429-1432	0.4	8
151	Selective Area Growth of Cubic GaN on 3C-SiC (001) by Metalorganic Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L1081-L1083	1.4	8
150	Enhanced activation of Mg ion-implanted GaN at decreasing annealing temperature by prolonging duration. <i>Applied Physics Express</i> , 2021 , 14, 011005	2.4	8
149	Reliability of Nitrided Gate Oxides for N- and P-Type 4H-SiC(0001) MetalOxideSemiconductor Devices. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 090201	1.4	8
148	Design and demonstration of nearly-ideal edge termination for GaN p \bar{n} junction using Mg-implanted field limiting rings. <i>Applied Physics Express</i> , 2021 , 14, 074002	2.4	8
147	Nitrogen-displacement-related electron traps in n-type GaN grown on a GaN freestanding substrate. <i>Applied Physics Letters</i> , 2021 , 118, 012106	3.4	8
146	Phonon-assisted optical absorption due to FranzKeldysh effect in 4H-SiC p \bar{n} junction diode under high reverse bias voltage. <i>Applied Physics Express</i> , 2018 , 11, 091302	2.4	7

145	Oxidation-induced majority and minority carrier traps in n- and p-type 4H-SiC. <i>Applied Physics Express</i> , 2015 , 8, 111301	2.4	7
144	Temperature dependence of current gain in 4H-SiC bipolar junction transistors. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 04DP13	1.4	7
143	Long Photoconductivity Decay Characteristics in p-Type 4H-SiC Bulk Crystals. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 010202	1.4	7
142	Demonstration of Common-Emitter Operation in AlGaN/SiC Heterojunction Bipolar Transistors. <i>IEEE Electron Device Letters</i> , 2010 , 31, 942-944	4.4	7
141	Systematic Investigation of c-Axis Tilt in GaN and AlGaN Grown on Vicinal SiC(0001) Substrates. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 020202	1.4	7
140	Improvement of channel property of GaN vertical trench MOSFET by compensating nitrogen vacancies with nitrogen plasma treatment. <i>Applied Physics Express</i> , 2020 , 13, 124003	2.4	7
139	Impact of Film Stress of Field-Plate Dielectric on Electric Characteristics of GaN-HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 5421-5426	2.9	7
138	Isochronal annealing study of Mg-implanted p-type GaN activated by ultra-high-pressure annealing. <i>Applied Physics Express</i> , 2021 , 14, 056501	2.4	7
137	Design Criterion for SiC BJTs to Avoid ON-Characteristics Degradation Due to Base Spreading Resistance. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2086-2091	2.9	6
136	Strong impact of the initial III/V ratio on the crystalline quality of an AlN layer grown by rf-plasma-assisted molecular-beam epitaxy. <i>Applied Physics Express</i> , 2016 , 9, 025502	2.4	6
135	Temperature dependence of forward characteristics for ultrahigh-voltage SiC p ⁺ n diodes with a long carrier lifetime. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 098004	1.4	6
134	Ultrahigh-Voltage SiC PiN Diodes with an Improved Junction Termination Extension Structure and Enhanced Carrier Lifetime. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 070204	1.4	6
133	Nonpolar 4H-Polytype AlN/AlGaN Multiple Quantum Well Structure Grown on 4H-SiC(1100). <i>Applied Physics Express</i> , 2010 , 3, 051001	2.4	6
132	Polytype Replication in Heteroepitaxial Growth of Nonpolar AlN on SiC. <i>MRS Bulletin</i> , 2009 , 34, 348-352	3.2	6
131	Bandgap shift by quantum confinement effect in <100> Si-nanowires derived from threshold-voltage shift of fabricated metal-oxide-semiconductor field effect transistors and theoretical calculations. <i>Journal of Applied Physics</i> , 2011 , 109, 064312	2.5	6
130	N ₂ O-grown oxides/4H-SiC (0001), (033 $\bar{1}$ 8), and (112 $\bar{1}$ 0) interface properties characterized by using p-type gate-controlled diodes. <i>Applied Physics Letters</i> , 2008 , 93, 193510	3.4	6
129	Surface Morphologies of 4H-SiC(1100) and (1100) Treated by High-Temperature Gas Etching. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 8388-8390	1.4	6
128	Electron Injection from GaN to SiC and Fabrication of GaN/SiC Heterojunction Bipolar Transistors. <i>Materials Science Forum</i> , 2006 , 527-529, 1545-1548	0.4	6

127	Effect of annealing time and pressure on electrical activation and surface morphology of Mg-implanted GaN annealed at 1300 °C in ultra-high-pressure nitrogen ambient. <i>Applied Physics Express</i> , 2021 , 14, 121004	2.4	6
126	Franz-Keldysh effect in n-type GaN Schottky barrier diode under high reverse bias voltage. <i>Applied Physics Express</i> , 2016 , 9, 091002	2.4	6
125	Formation of highly vertical trenches with rounded corners via inductively coupled plasma reactive ion etching for vertical GaN power devices. <i>Applied Physics Letters</i> , 2021 , 118, 102101	3.4	6
124	Demonstration of Conductivity Modulation in SiC Bipolar Junction Transistors With Reduced Base Spreading Resistance. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4870-4874	2.9	5
123	Electron traps formed by gamma-ray irradiation in homoepitaxial n-type GaN and their annealing behavior. <i>AIP Advances</i> , 2020 , 10, 045023	1.5	5
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